

1-Line Ultra Low Capacitance Bi-directional TVS Diode

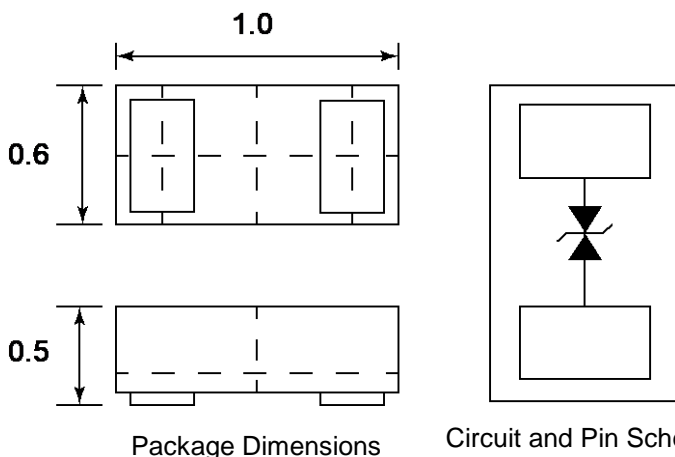
Description

The PESDR3321P1 is a bi-directional TVS diode, to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive high-speed data lines. The PESDR3321P1 has an ultra-low capacitance with a typical value at 0.35pF, and complies with the IEC 61000-4-2 (ESD) with $\pm 20\text{kV}$ air and $\pm 15\text{kV}$ contact discharge. It is assembled into a DFN1006-2 lead-free package. The small size, ultra-low capacitance and high ESD surge protection make PESDR3321P1 an ideal choice to protect cell phone, digital video interfaces and other high speed ports.

Features

- Ultra low capacitance: 0.35pF typical
- Ultra low leakage: nA level
- Operating voltage: 3.3V
- Low clamping voltage
- Complies with following standards:
 - IEC 61000-4-2 (ESD) immunity test
Air discharge: $\pm 20\text{kV}$
Contact discharge: $\pm 15\text{kV}$
 - IEC 61000-4-5 (Lightning) 4A (8/20 μs)
- RoHS Compliant

Dimensions and Pin Configuration



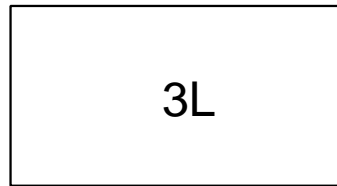
Mechanical Characteristics

- Package: DFN1006-2 (1.0x0.6x0.5mm)
- Case Material: "Green" Molding Compound.
- Moisture Sensitivity: Level 1 per J-STD-020
- Marking Information: See Below

Applications

- Cellular Handsets and Accessories
- Display Ports
- MDDI Ports
- USB Ports
- Digital Visual Interface (DVI)
- PCI Express and Serial SATA Ports

Marking Information



3L = Device Marking Code

Ordering Information

Part Number	Packaging	Reel Size
PESDR3321P1	10000/Tape & Reel	7 inch

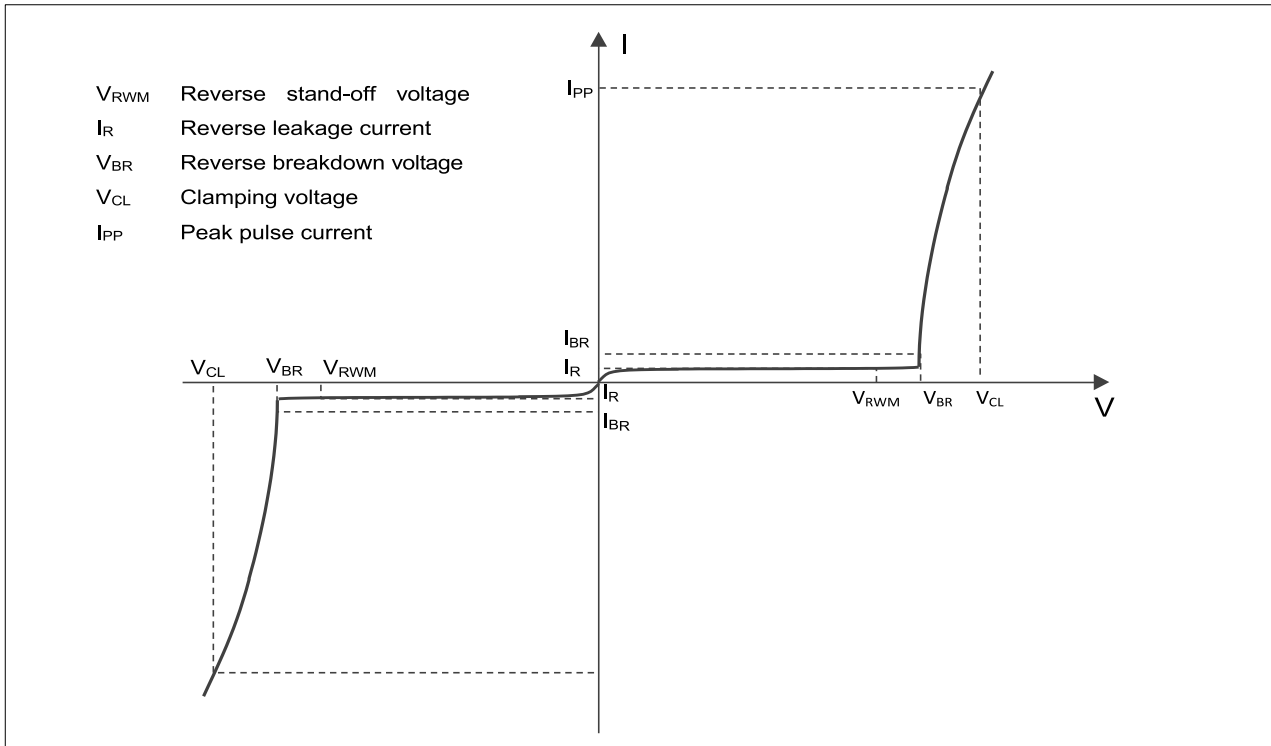
Absolute Maximum Ratings (T_A=25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20μs)	P _{PK}	100	W
Peak Pulse Current (8/20μs)	I _{PP}	4	A
ESD per IEC 61000-4-2 (Air)	V _{ESD}	±20	kV
ESD per IEC 61000-4-2 (Contact)		±15	
Lead temperature	T _L	260	°C
Operating Temperature Range	T _J	-40 ~ +85	°C
Storage Temperature Range	T _{STG}	-55 ~ +150	°C

Electrical Characteristics (T_A=25°C unless otherwise specified)

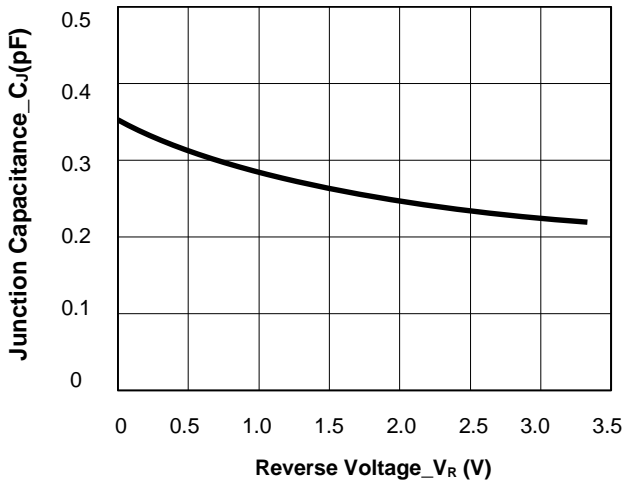
Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	V _{RWM}			3.3	V	
Breakdown Voltage	V _{BR}	5			V	I _T = 1mA
Reverse Leakage Current	I _R			0.2	μA	V _{RWM} = 3.3V
Clamping Voltage	V _C			11	V	I _{PP} = 1A (8/20μs pulse)
Clamping Voltage	V _C			25	V	I _{PP} = 4A (8/20μs pulse)
Junction Capacitance	C _J		0.35		pF	V _R = 0V, f = 1MHz

Electrical characteristics ($T_A = 25^\circ\text{C}$, unless otherwise noted)

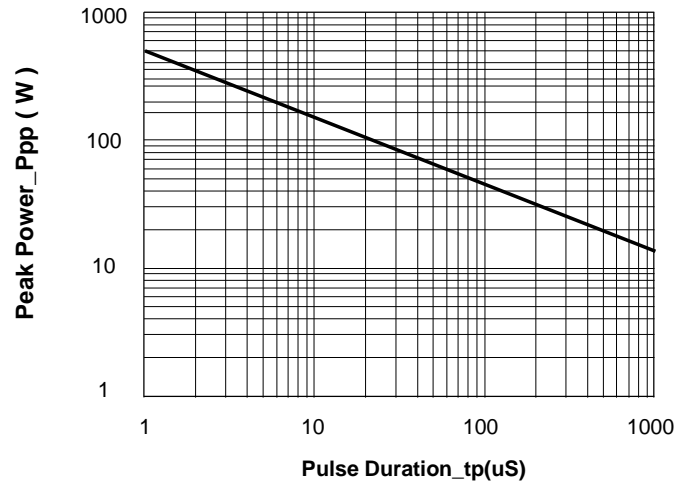


Definitions of electrical characteristics

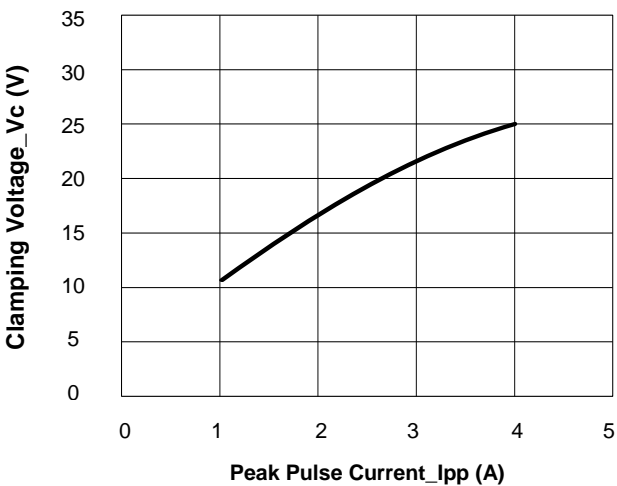
Typical Performance Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise Specified)



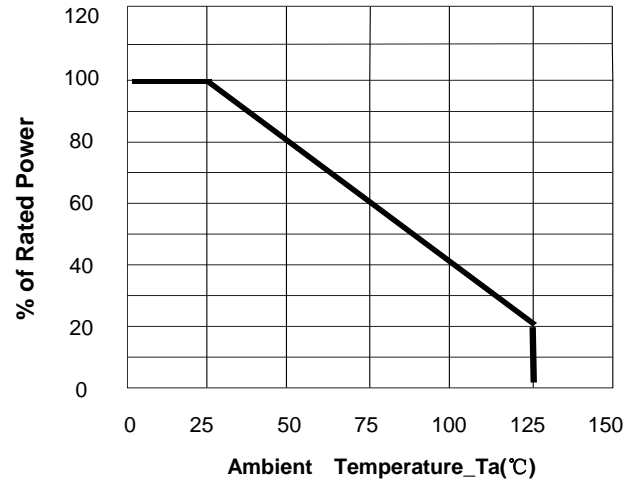
Junction Capacitance vs. Reverse Voltage



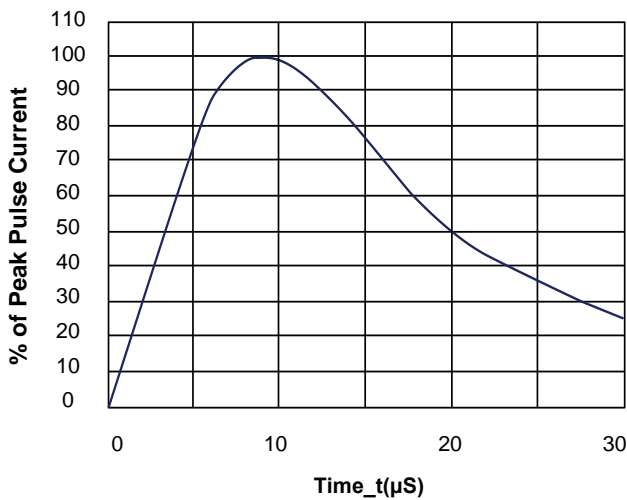
Peak Pulse Power vs. Pulse Time



Clamping Voltage vs. Peak Pulse Current

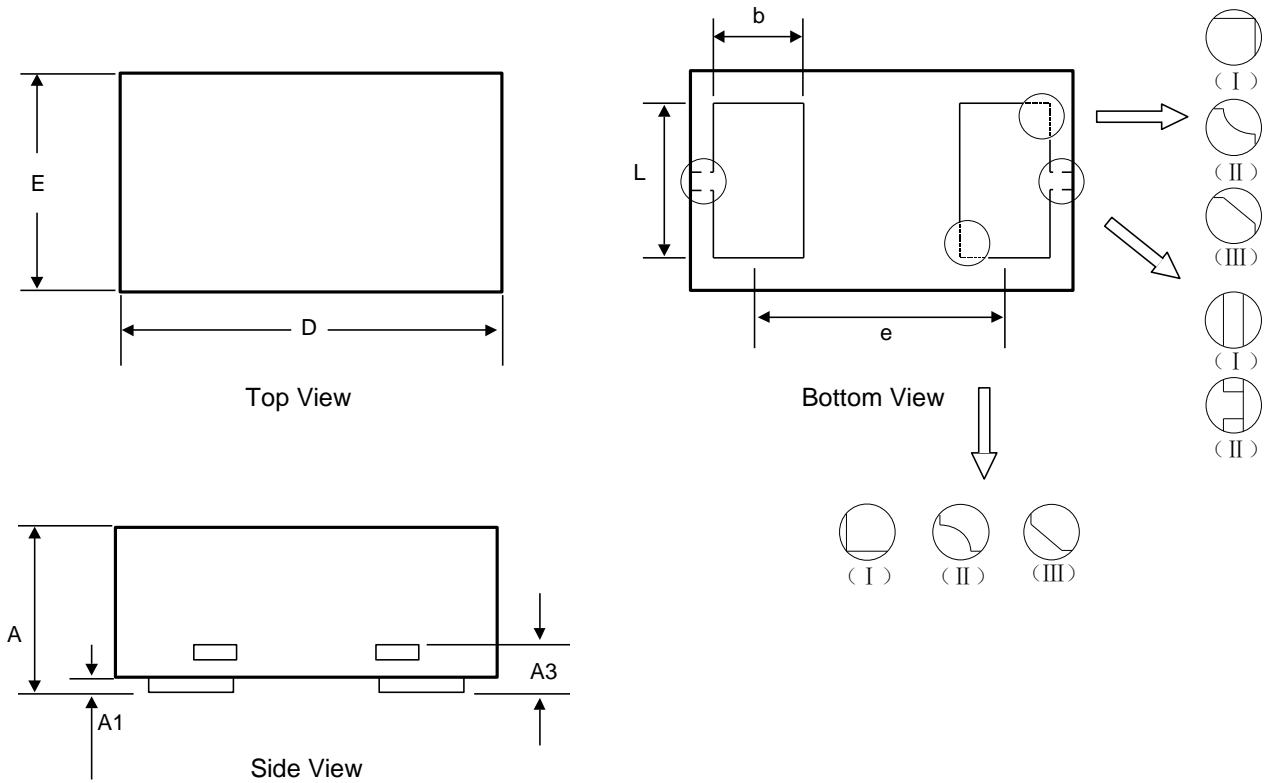


Power Derating Curve



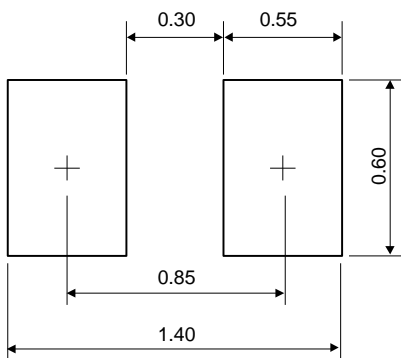
8/20μS Pulse Waveform

DFN1006-2 Package Outline Drawing



Symbol	Dimensions in Millimeters		
	Min.	Typ.	Max.
A	0.340	0.450	0.550
A1	0.000	0.020	0.050
A3	0.125 Ref.		
D	0.950	1.000	1.075
E	0.490	0.600	0.675
b	0.200	0.250	0.300
L	0.450	0.500	0.550
e	0.650 BSC		

Recommended PCB Layout (Unit: mm)

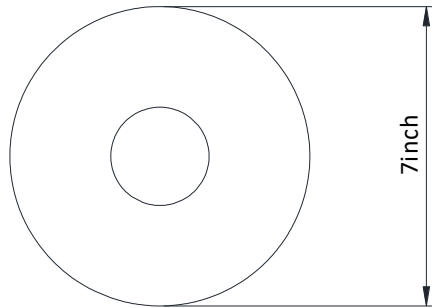


Notes:

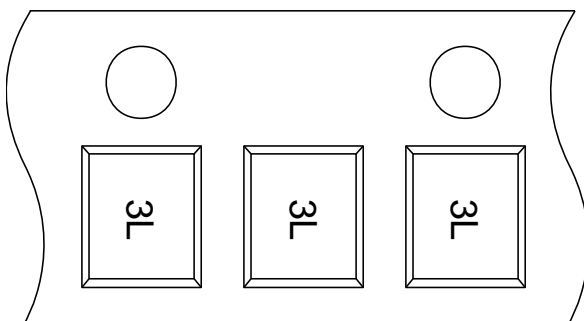
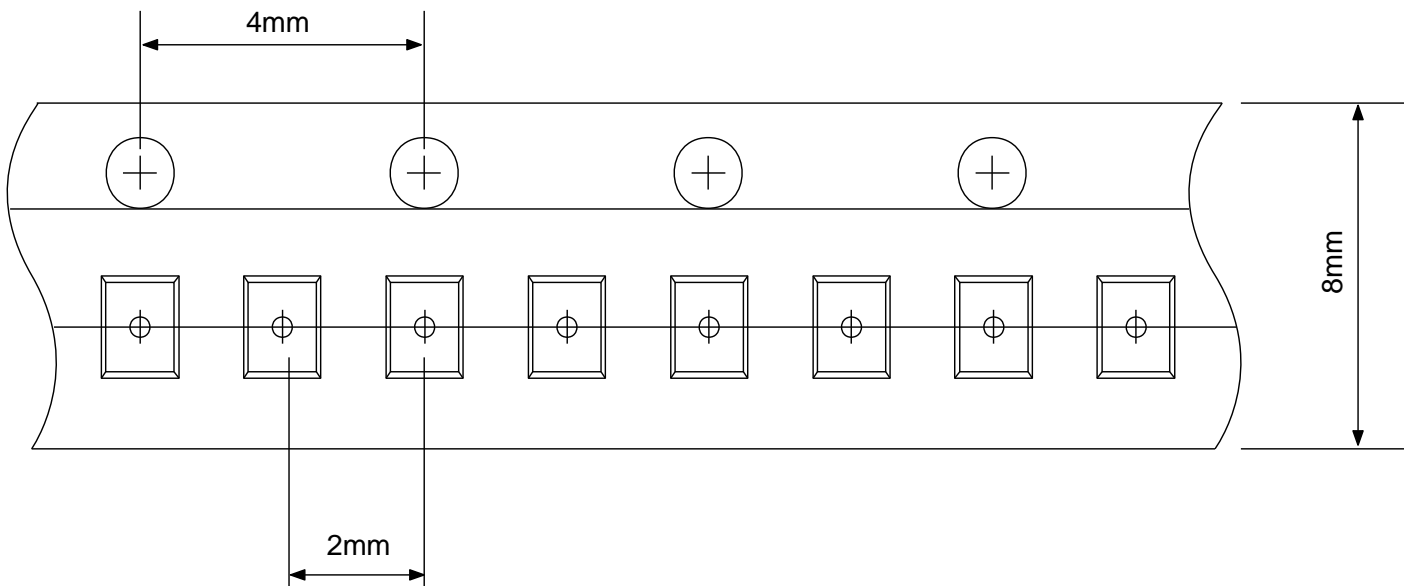
This recommended land pattern is for reference purposes only. Please consult your manufacturing group to ensure your PCB design guidelines are met.


TAPE AND REEL INFORMATION

Reel Dimensions



Tape Dimensions





User Direction of Feed

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